

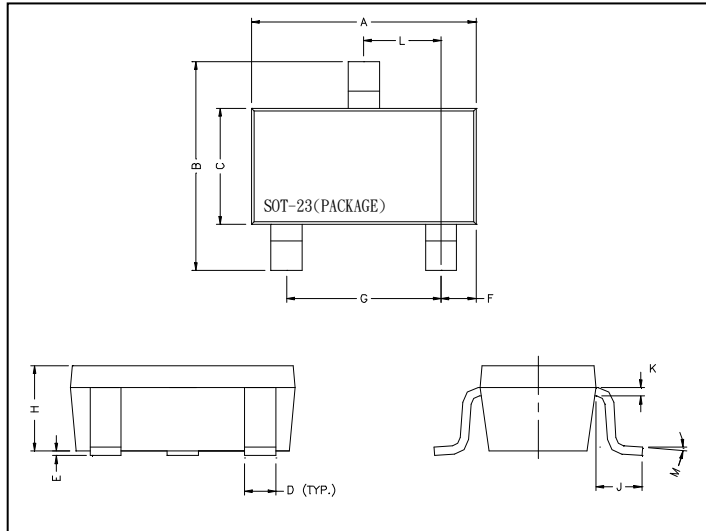
GMBTA05

NPN SILICON TRANSISTOR

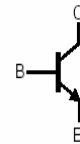
Description

The GMBTA05 is Amplifier Transistor.

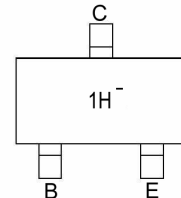
Package Dimensions



CIRCUIT



Marking:



REF	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25°C

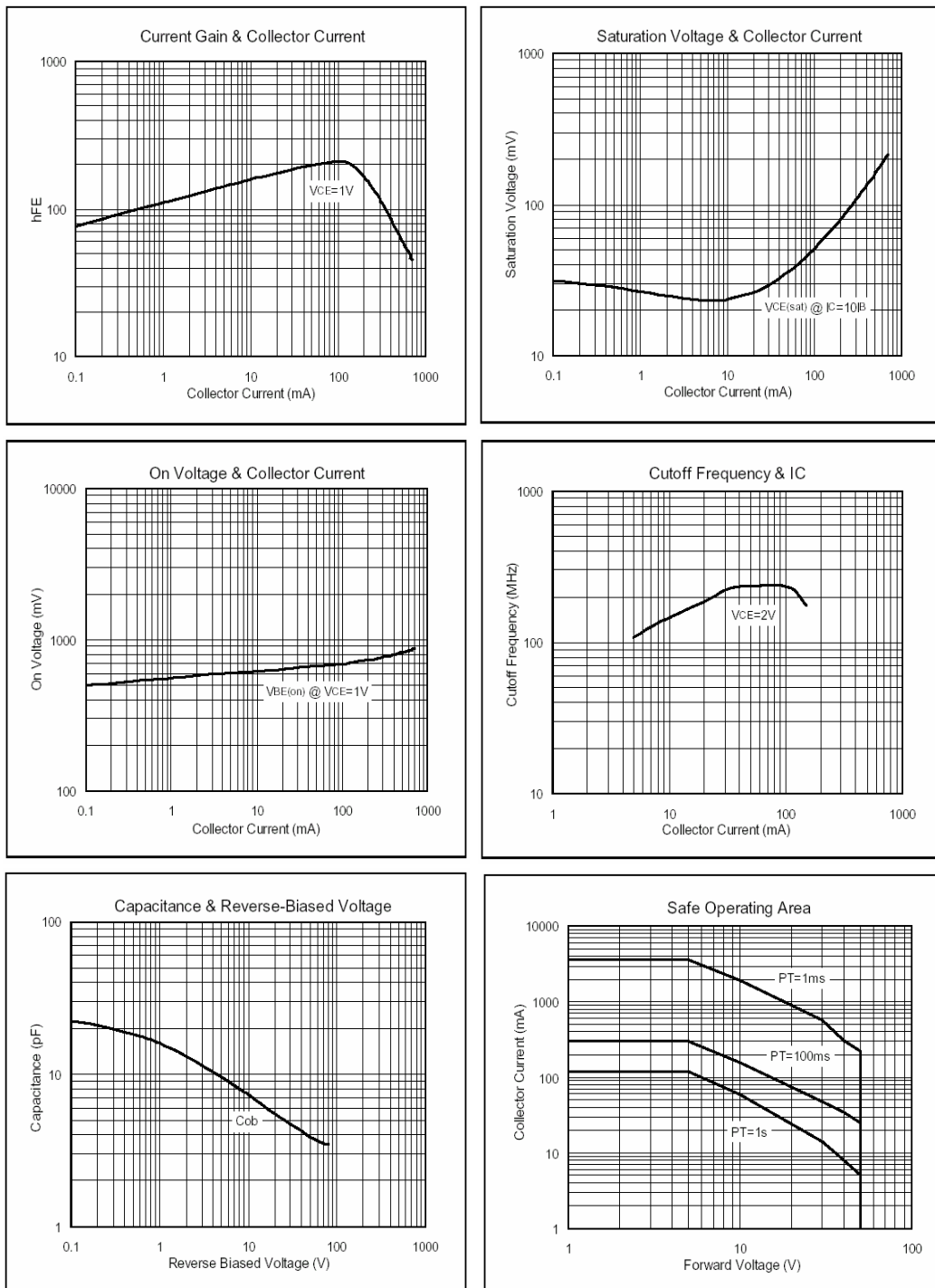
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCEO	60	V
Emitter to Base Voltage	VEBO	4	V
Collector Current	IC	500	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=100uA
BVCEO	60	-	-	V	IC=1mA
BVEBO	4	-	-	V	IE=100uA
ICBO	-	-	100	nA	VCB=60V
ICEO	-	-	100	nA	VCE=60V
*VCE(sat)	-	-	250	mV	IC=100mA, IB=10mA
VBE(sat)	-	-	1.2	V	IC=100mA, VCE=1V
*hFE1	50	-	-		VCE=1V, IC=10mA
*hFE2	50	-	-		VCE=1V, IC=100mA
fT	100	-	-	MHz	VCE=2V, IC=10mA, f=100MHz

*Pulse Test:Pulse width ≤380us,Duty Cycle≤2%

Characteristics Curve



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